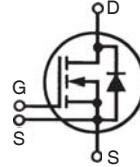


# X2-Class HiPerFET™ Power MOSFET

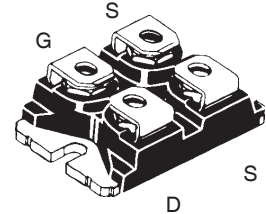
## IXFN150N65X2

$V_{DSS} = 650V$   
 $I_{D25} = 145A$   
 $R_{DS(on)} \leq 17m\Omega$

N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode



miniBLOC, SOT-227  
 E153432



G = Gate      D = Drain  
 S = Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	650	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	650	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	145	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	300	A
$I_A$	$T_C = 25^\circ C$	20	A
$E_{AS}$	$T_C = 25^\circ C$	4	J
$P_D$	$T_C = 25^\circ C$	1040	W
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	50	V/ns
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ minute	2500	V~
	$I_{ISOL} \leq 1mA$ $t = 1$ second	3000	V~
$M_d$	Mounting Torque	1.5/13	Nm/lb.in
	Terminal Connection Torque	1.3/11.5	Nm/lb.in
<b>Weight</b>		30	g

### Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500 V~
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low  $R_{DS(on)}$

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

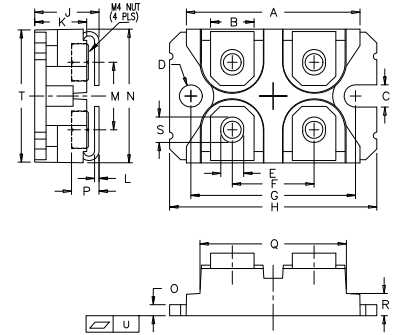
### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 3mA$	650		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	3.5		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 5 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 75A$ , Note 1			17 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1	56	88	S
$R_{Gi}$	Gate Input Resistance		0.57	$\Omega$
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		21.0	nF
$C_{oss}$			12.5	nF
$C_{rss}$			42	pF
<b>Effective Output Capacitance</b>				
$C_{o(er)}$	Energy related		600	pF
$C_{o(tr)}$	Time related		2800	pF
<b>Resistive Switching Times</b>				
$t_{d(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 75\text{A}$ $R_G = 1\Omega$ (External)		55	ns
$t_r$			30	ns
$t_{d(off)}$			100	ns
$t_f$			13	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 75\text{A}$		355	nC
$Q_{gs}$			130	nC
$Q_{gd}$			110	nC
$R_{thJC}$				0.12 $^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

### SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

### Source-Drain Diode

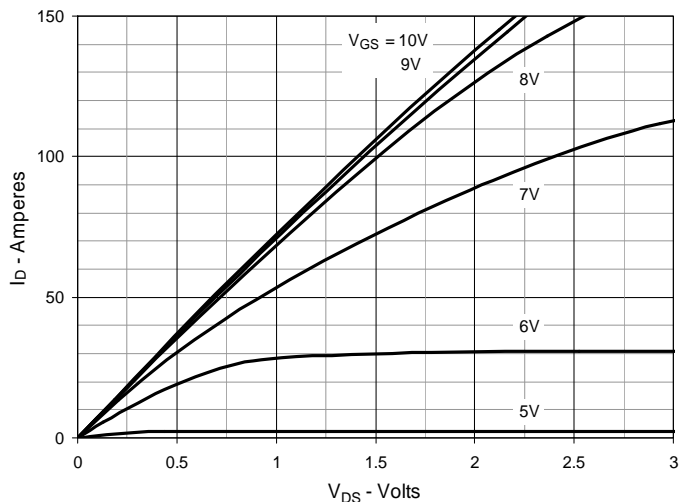
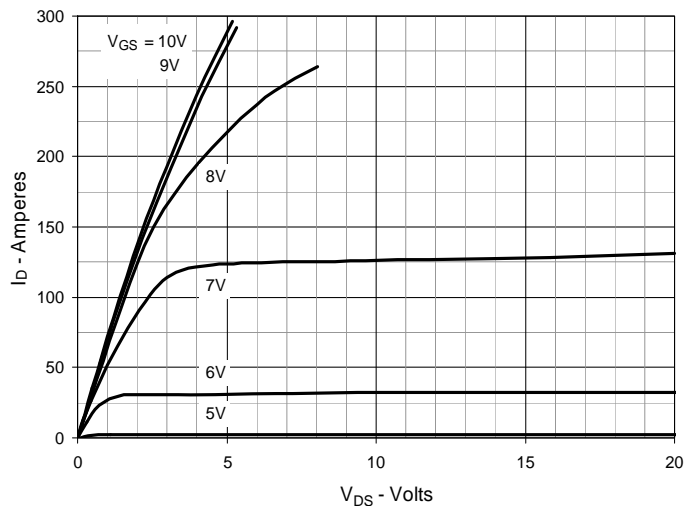
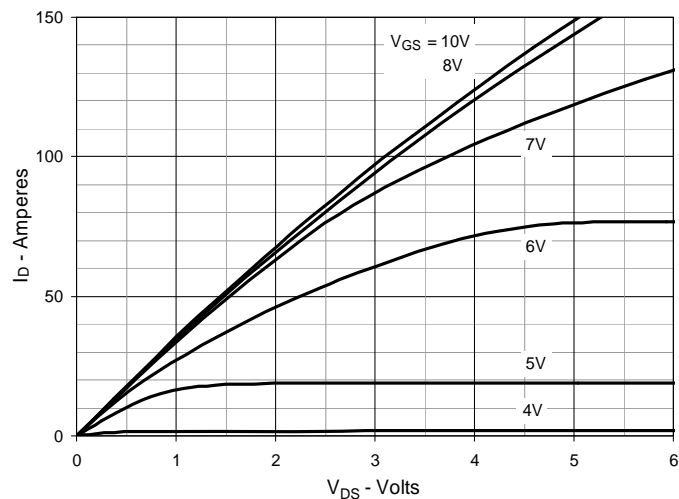
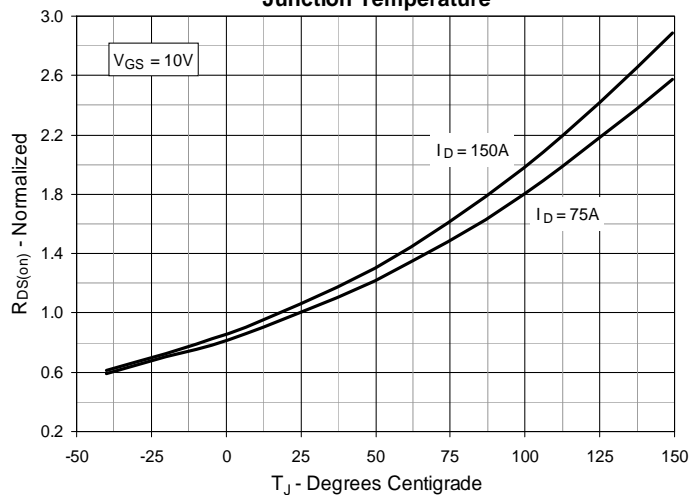
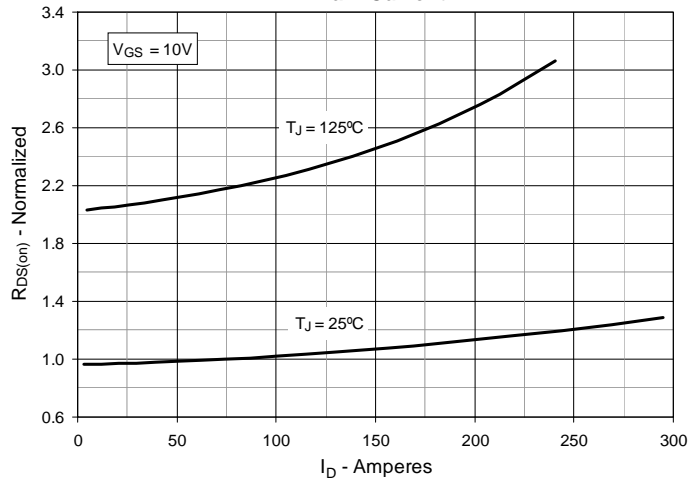
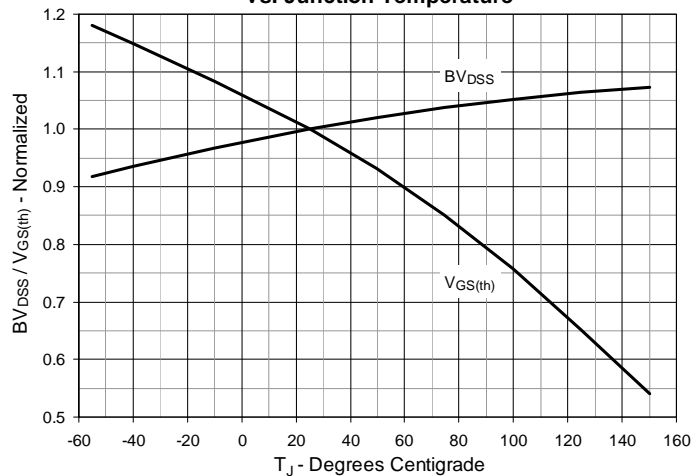
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			150 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			600 A
$V_{SD}$	$I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			1.4 V
$t_{rr}$	$I_F = 75\text{A}$ , $-di/dt = 300\text{A}/\mu\text{s}$		190	ns
$Q_{RM}$			4.6	$\mu\text{C}$
$I_{RM}$	$V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$		48.4	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

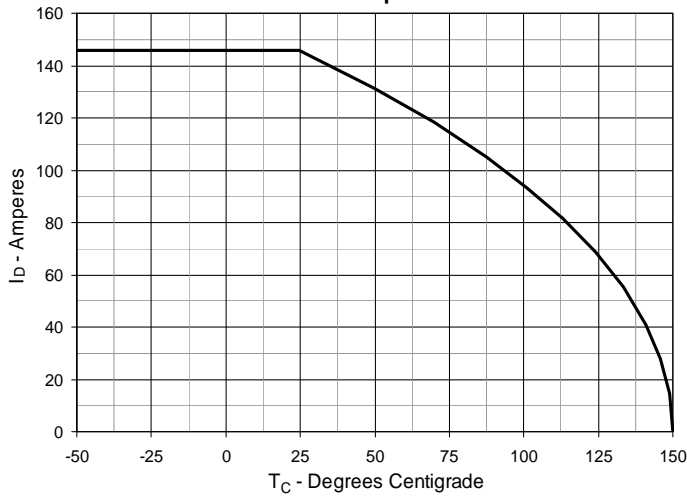
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

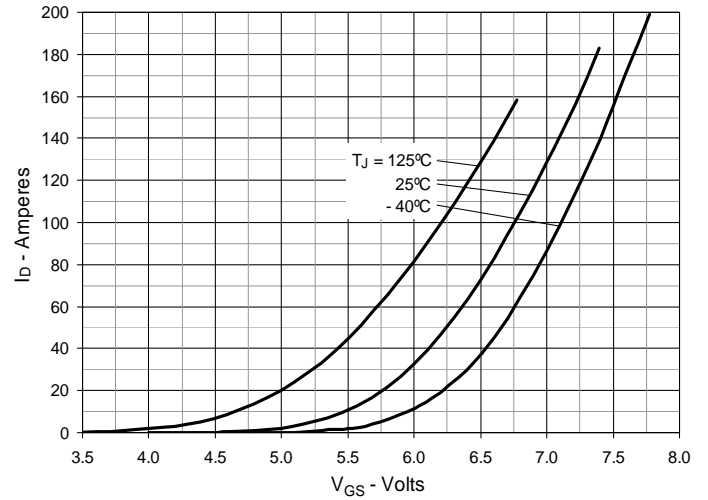
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 75\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 75\text{A}$  Value vs. Drain Current**

**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**


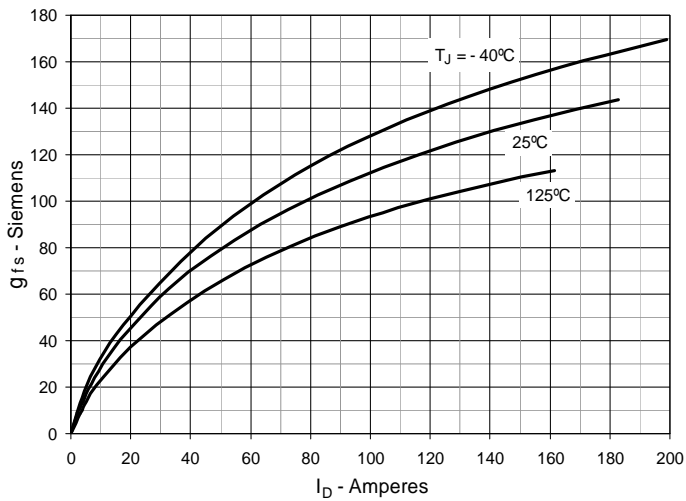
**Fig. 7. Maximum Drain Current vs. Case Temperature**



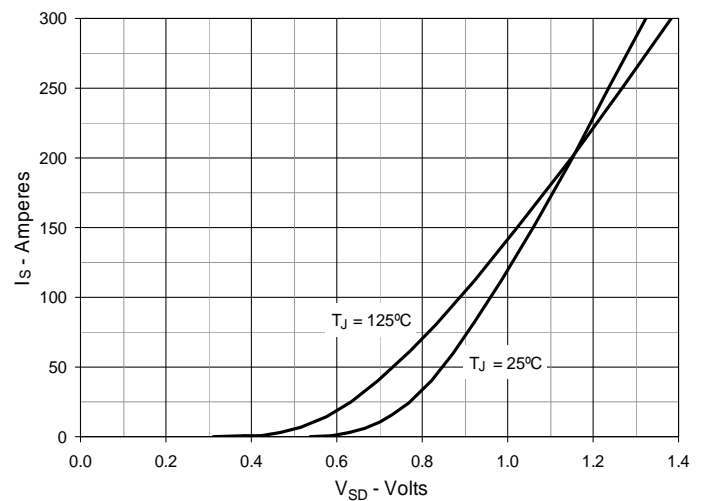
**Fig. 8. Input Admittance**



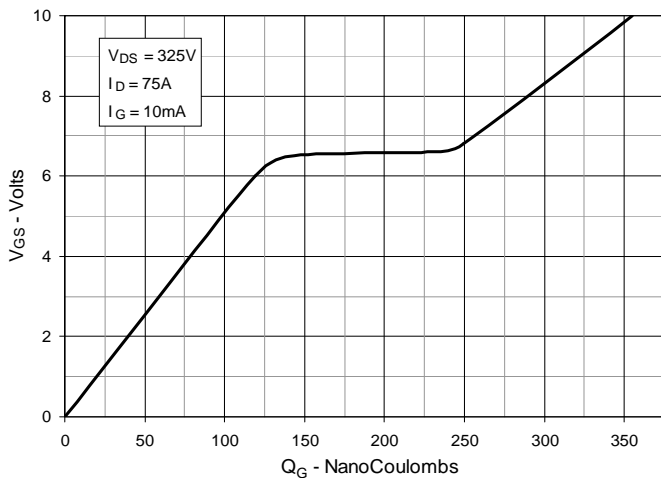
**Fig. 9. Transconductance**



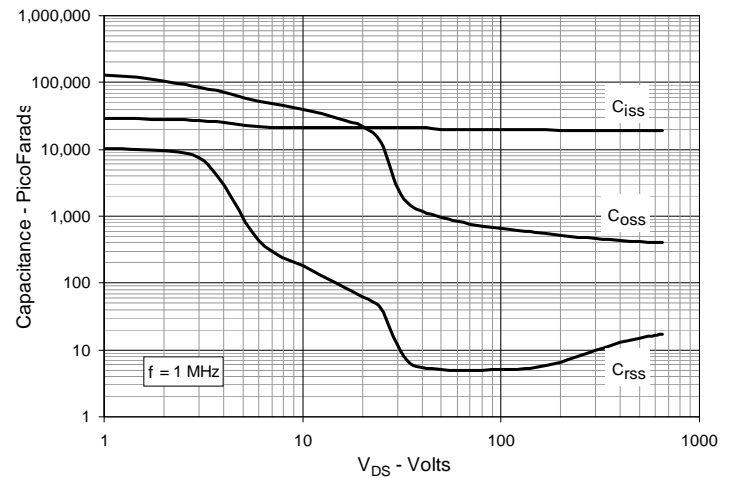
**Fig. 10. Forward Voltage Drop of Intrinsic Diode**



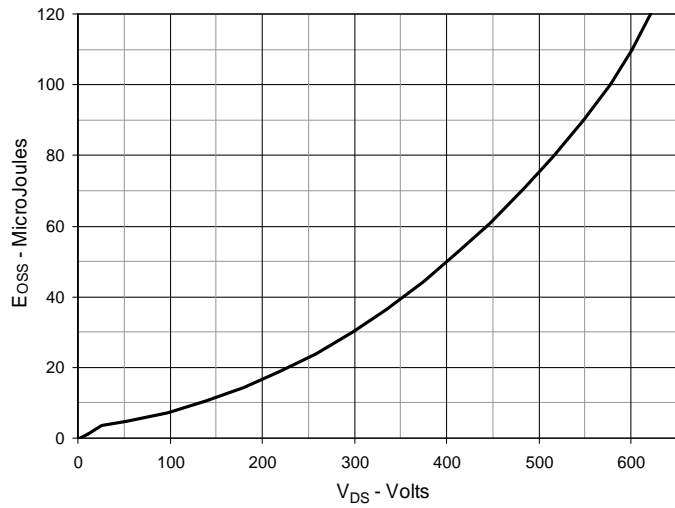
**Fig. 11. Gate Charge**



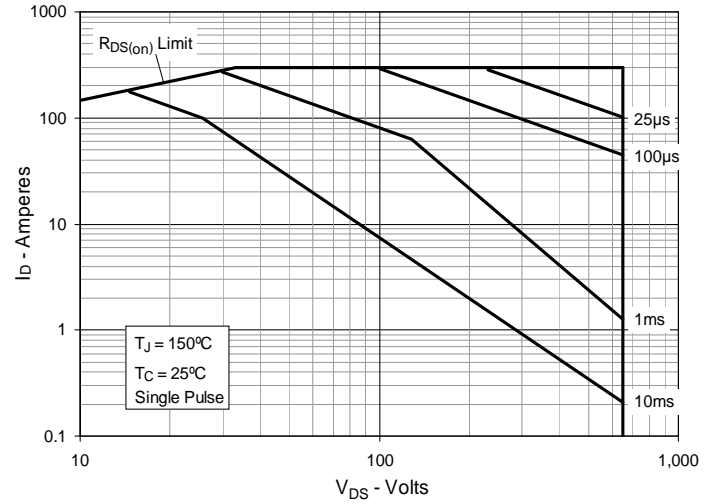
**Fig. 12. Capacitance**



**Fig. 13. Output Capacitance Stored Energy**



**Fig. 14. Forward-Bias Safe Operating Area**



**Fig. 15. Maximum Transient Thermal Impedance**

